

# Effect of Pressure on Interband Reflectivity Spectra of Semiconductors

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Citation Report

#	ARTICLE	IF	CITATIONS
1	A pseudopotential examination of the pressure coefficients of optical transitions in semiconductors. Journal of Physics and Chemistry of Solids, 1967, 28, 1441-1450.	4.0	36
2	Optical Properties of GeSi Alloys in the Energy Region from 1 to 13 eV. Physica Status Solidi (B): Basic Research, 1968, 27, 57-67.	1.5	43
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5	Piezoreflectance of Germanium from 1.9 to 2.8 eV. Physical Review, 1969, 185, 1103-1114.	2.7	64
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146	Gallium antimonide (GaSb), spin-orbit splitting energies. , 0, , 1-5.		0
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